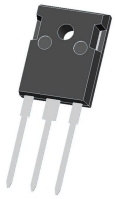
Technical Data
Data Sheet N2363,REV.B

S3D35065D1
650V SIC POWER SCHOTTKY RECTIFIER

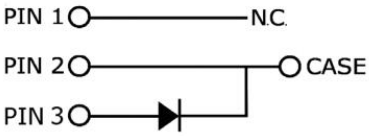


TO-247AD(TO-247-3)

Description

S3D35065D1 is a SiC Schottky rectifier packaged in TO-247AD(TO-247-3) case. The device is a high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D35065D1 is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- **175°C T_J operation**
- **Ultra-low switching loss**
- **Switching speeds independent of operating temperature**
- **Low total conduction losses**
- **High forward surge current capability**
- **High package isolation voltage**
- **Terminals finish: 100% Pure Tin**
- **"-A" is an AEC-Q101 qualified device**
- **Pb − Free Device**
- **All SMC parts are traceable to the wafer lot**
- **Additional electrical and life testing can be performed upon request**

Applications

- **Alternative energy inverters**
- **Power Factor Correction (PFC)**
- **Free-Wheeling diodes**
- **Switching supply output rectification**
- **Reverse polarity protection**

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_{DC}	-	650	V
Average Rectified Forward Current	$I_{F\ (AV)1}$	Tc=25°C	60	A
	$I_{F\ (AV)2}$	Tc=115°C	35	A
Repetitive Peak Forward Surge Current	I_{FRM1}	10ms, Half Sine pulse, T_C =25°C	135	A
	I_{FRM2}	10ms, Half Sine pulse, T_C =110°C	90	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM1}	10ms, Half Sine pulse, T_C =25°C	270	A
	I_{FSM2}	10ms, Half Sine pulse, T_C =110°C	185	A
Non-Repetitive Peak Forward Surge Current	$I_{F,Max1}$	10μs. Pulse, T_C =25℃	2295	A
	$I_{F,Max2}$	10μs. Pulse, T_C =110℃	1570	A
Power Dissipation	P_{tot1}	T_C =25℃	178	W
	P_{tot2}	T_C =110℃	77	W
TO-247 Mounting Torque		M3 Screw	1	Nm
		6-32 Screw	8.8	bf-in

Technical Data
Data Sheet N2363,REV.B

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 35A, Pulse, T_J = 25 °C	1.55	1.7	V
	V_{F2}	@ 35A, Pulse, T_J = 175 °C	2.0	24	V
Reverse Current at DC condition*	I_{R1}	@V_R = rated V_R T_J = 25 °C	0.6	80	uA
Reverse Current *	I_{R2}	@V_R = rated V_R T_J = 175 °C	12	200	uA
Junction Capacitance	C_T	VR=0V, T_J=25℃,f=100MHz	2022	-	pF
Reverse Recovery Charge	Q_c	I_F = 35A, di/dt = 200A/μs V_R = 400 V, T_J =25°C	126.15	-	nC
Capacitance Stored Energy	E_C	V_R = 400 V, T_J =25°C	30.90	-	μJ

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	°C
Storage Temperature	T_{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	0.84(per leg) 0.42(both leg)	°C/W

Ordering Information

Device	Package	Shipping
S3D35065D1	TO-247AD(TO-247-3)	25pcs /tube

Ratings and Characteristics Curves

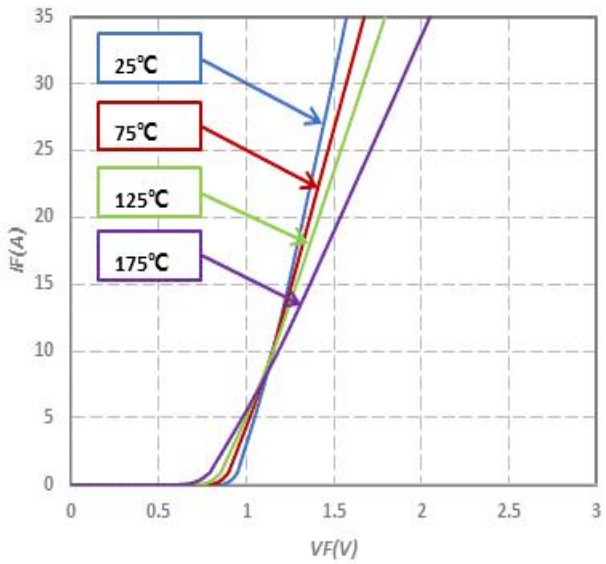


Fig.1-Typical Forward Voltage Characteristics

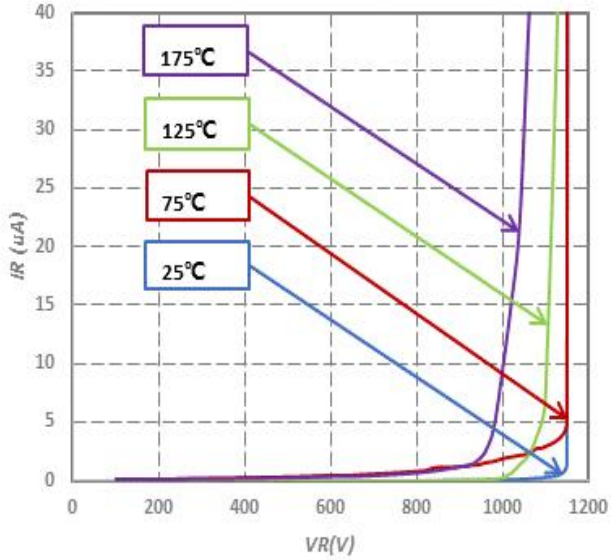


Fig.2-Typical Reverse Characteristics

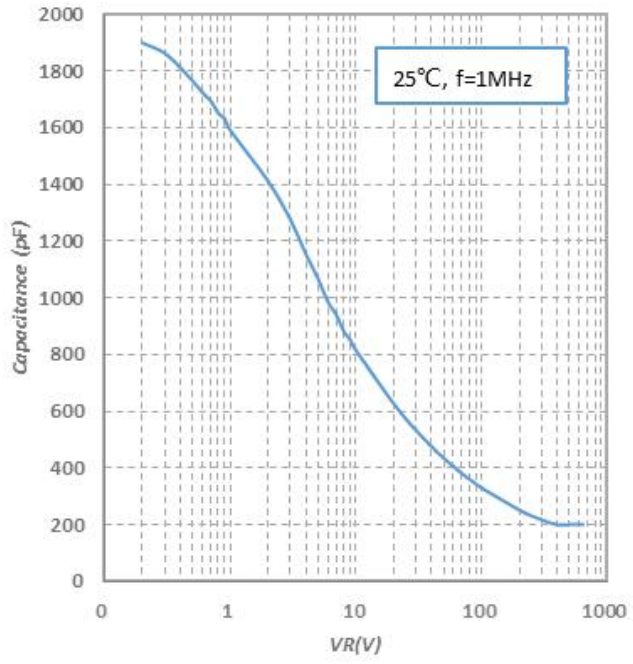


Fig.3-Capacitance vs. Reverse Voltage

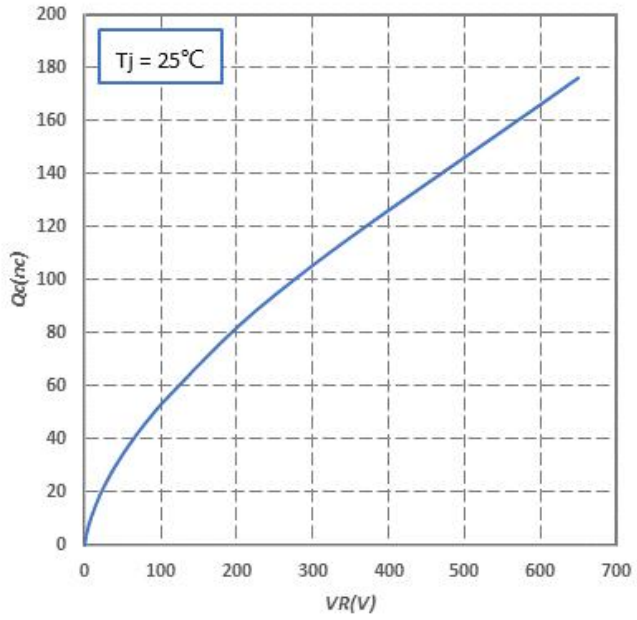


Fig.4-Total Capacitance Charge vs. Reverse Voltage

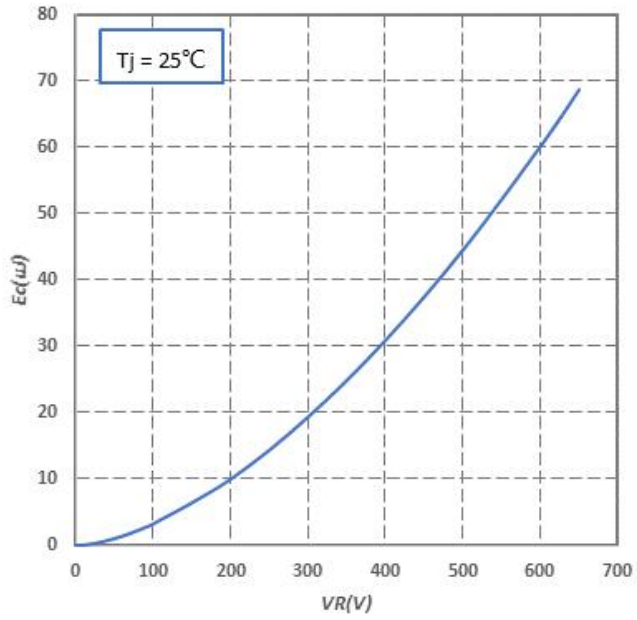


Fig.5-Capacitance Stored Energy

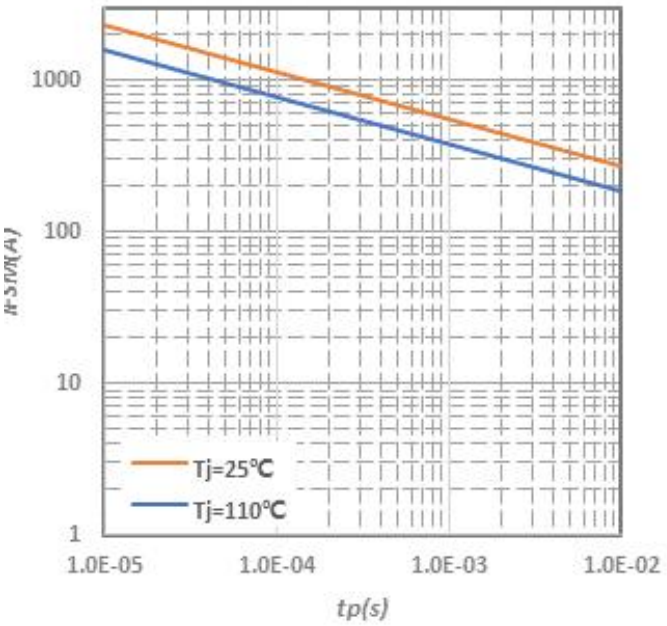


Fig.6-Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

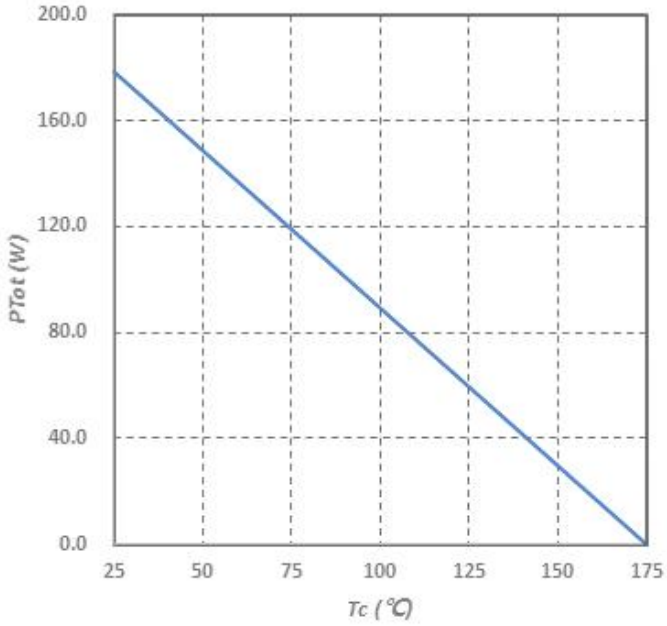


Fig.7-Power Derating

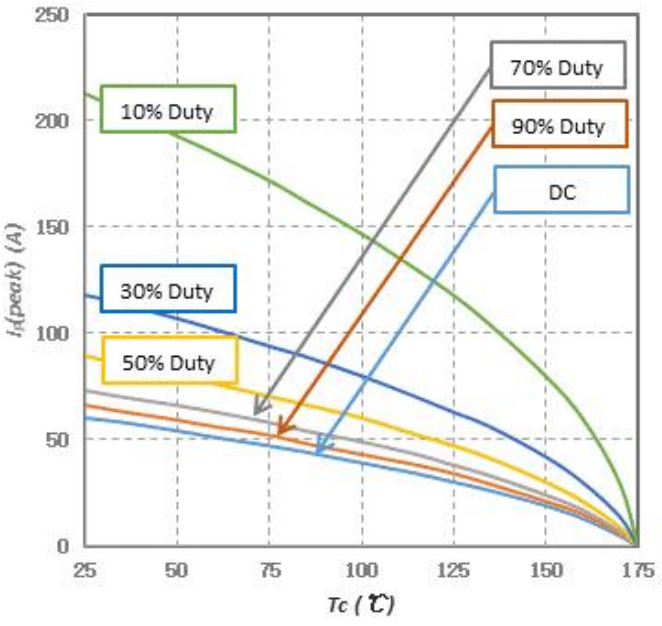
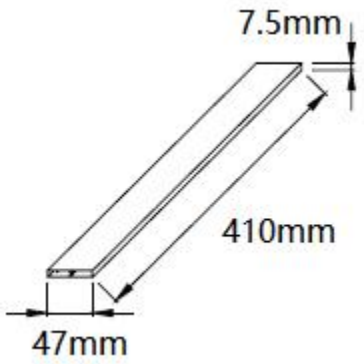


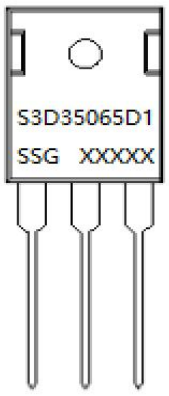
Fig.8-Current Derating

Technical Data
Data Sheet N2363,REV.B

Tube Specification



Marking Diagram

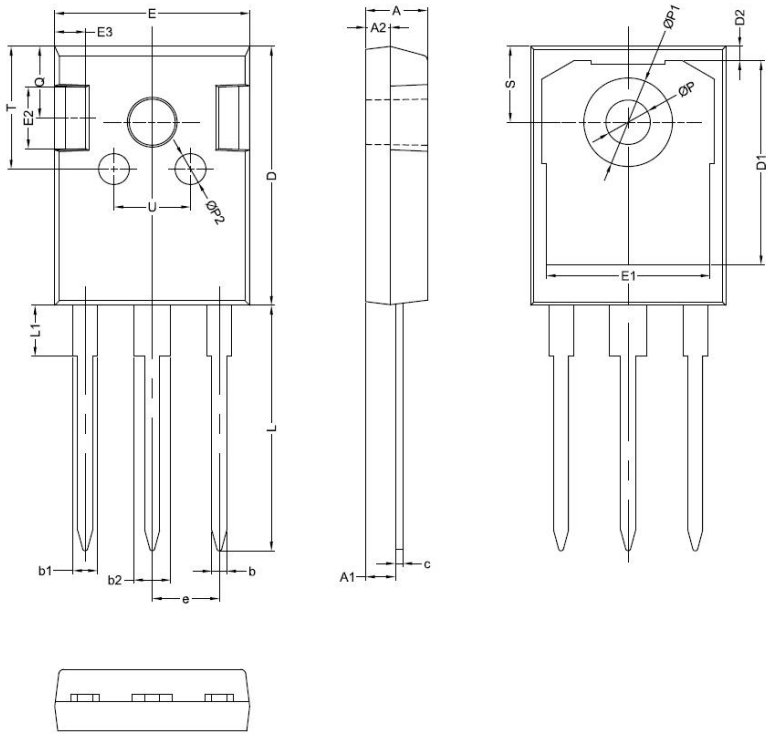


Where XXXXX is YYWWL

S3D	= Device Type
D1	= Package type
35	= Forward Current (35A)
065	= Reverse Voltage (650V)
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Mechanical Dimensions TO-247AD



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80		5.20
A1	2.00		2.75
A2	1.90		2.10
b	1.00		1.40
b1	1.80		2.40
b2	2.80		3.40
c	0.40		0.75
D	19.80		21.20
D1		16.55	
D2		1.20	
E	15.20		16.00
E1		13.30	
E2		5.00	
E3		2.50	
e	5.20		5.70
L	13.90		20.70
L1	3.70		4.30
P	3.50		3.70
P1	7.1		7.40
P2		2.50	
Q		5.80	
S	6.05		6.25
T		10.00	
U		6.20	

Technical Data
Data Sheet N2363,REV.B

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